

IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently Amended): A method for manufacturing a prescribed semiconductor device by forming a film mainly formed of tungsten and a film of silicon a ~~component different from the film mainly formed of the tungsten~~ on a semiconductor substrate, comprising:

forming a first layer, which is formed of the film of the silicon ~~component different from the film mainly formed of the tungsten~~, on the semiconductor substrate;

forming a second layer, which is formed of the film mainly formed of the tungsten, on the semiconductor substrate; and

selectively forming an oxide film on an exposed surface of the first layer by plasma processing at a process temperature of 300°C or more using a process gas containing an inert gas, oxygen gas and hydrogen gas at a flow rate ratio (hydrogen gas flow rate/oxygen gas flow rate) of the hydrogen gas to the oxygen gas of 2 or more and 4 or less so as not to form the oxide film on an exposed surface of the second layer.

Claim 2 (Original): The method for manufacturing a semiconductor device according to claim 1, wherein the semiconductor device is a transistor, and a gate electrode is formed of the first layer and the second layer.

Claim 3 (Previously Presented): The method for manufacturing a semiconductor device according to claim 1, wherein the second layer is a tungsten layer or a tungsten silicide layer.

Claims 4-6 (Canceled)

Claim 7 (Currently Amended): A method for plasma oxidation of a film of silicon a ~~component different from a film mainly formed of tungsten~~ of a semiconductor substrate on which the film mainly formed of the tungsten and the film of the silicon ~~component different from the film mainly formed of the tungsten~~ are formed, comprising:

selectively forming an oxide film on an exposed surface of the film of the silicon ~~component different from the film mainly formed of the tungsten~~ by plasma processing at a process temperature of 300°C or more using a process gas containing an inert gas, oxygen gas and hydrogen gas at a flow rate ratio (hydrogen gas flow rate/oxygen gas flow rate) of the hydrogen gas to the oxygen gas of 2 or more and 4 or less so as not to form the oxide film on an exposed surface of the film mainly formed of the tungsten.

Claim 8 (Previously Presented): The plasma oxidation method according to claim 7, wherein the plasma is excited by a microwave.

Claim 9 (Canceled)

Claim 10 (New): The plasma oxidation method according to claim 1, wherein the first layer is a polysilicon layer.

Claim 11 (New): A method for plasma processing, in a chamber, of a substrate including a high temperature metallic member and a film containing silicon, comprising:

supplying an inert gas, oxygen gas and hydrogen gas into the chamber at a flow rate ratio (hydrogen gas flow rate/oxygen gas flow rate) of a hydrogen gas to the oxygen gas of 2 or more and 4 or less to generate a plasma directly on the substrate in the chamber; and

selectively oxidizing the film containing the silicon using the plasma to form an oxide film at a process temperature of 300°C or more so as not to oxidize the high temperature metallic member.

Claim 12 (New): The plasma oxidation method according to claim 1, wherein the process gas consists of the inert gas, the oxygen gas and the hydrogen gas.

Claim 13 (New): The method for plasma processing of Claim 11, wherein the supplying an inert gas, oxygen gas and hydrogen gas are the only gases supplied into the chamber to generate the plasma.